

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	416935	strain\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/15 14:24
L2	192050	inplant or implant or implanting or implanting	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/15 14:24
L3	240183	mosfet or (metal adj oxide adj semiconductor adj (fet or field)) or pmos or cmos or nmos or misfet or complement\$6 near (mosfet misfet metal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/15 14:24
L4	3780923	si silicon germanium sige gesi sic carbon iv!	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/15 14:24
L5	8060	L1 near4 L4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/15 14:24
L6	20	(L5 same L2 and L3).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/15 14:34
L7	2379	((438/167) or (438/172) or (438/300) or (438/752) or (438/753)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/15 14:24
L8	33475	soi silicon adj on adj insulat\$4 buried adj insulat\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/15 14:35
S25 3	33269	silicon near2 germanium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/18 18:27

S25 4	542	"si.sub.x ge.sub.1-x"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/18 18:15
S25 5	410	"si.sub.xge.sub.1-x"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/18 18:15
S25 6	76	"si.sub.x ge.sub.y"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/18 18:15
S25 7	74	"si.sub.y ge.sub.1-y" "si.sub.yge.sub. 1-y"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/18 18:15
S25 8	1098	"si.sub.1-x ge.sub.x" "si.sub.1-xge. sub.x"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/18 18:15
S25 9	204	"si.sub.1-y ge.sub.y" "si.sub.1-yge. sub.y"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/18 18:15
S26 0	33935	S254 or S255 or S256 or S257 or S258 or S259 or S253	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/18 18:28
S26 1	235205	mosfet or (metal adj (oxide or insulat\$4) adj semiconductor adj (fet or field)) or pmos or cmos or nmos or misfet	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/18 18:15
S26 2	190131	inplant or implant or implanting or implanting	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/18 18:19
S26 3	205	S261 and S260 near4 S262	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/18 18:20

S26 4	23362	strained	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/18 18:20
S26 5	44	S261 and S260 near2 S264 and S260 near4 S262	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/18 18:20
S26 6	414174	strain\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 17:11
S26 7	46	S261 and S260 near2 S266 and S260 near4 S262	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/18 18:27
S26 8	16	S267 and (@ad < "20021030")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/18 18:29
S26 9	343	S260 near4 S262	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/18 18:27
S27 0	28948	silicon near germanium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/18 18:27
S27 1	29677	S254 or S255 or S256 or S257 or S258 or S259 or S270	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/18 18:28
S27 2	697	S271 near2 S266	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/18 18:29
S27 3	512	S271 with S262	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/18 18:29

S27 4	73	S261 and S272 and S273	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/18 19:13
S27 5	25	S274 and (@ad < "20021030")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/18 19:16
S27 6	49736	graded	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/18 19:13
S27 7	34	S261 and S272 and S273 and S276	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/18 19:44
S27 8	27	S277 and (@ad < "20031030")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/18 19:16
S27 9	0	(S261 and S272 and S273 and S276). clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/18 19:44
S28 0	414840	strain\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 17:11
S28 1	2057	S280 near4 channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 17:26
S28 2	190586	inplant or implant or inplanting or implanting	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 17:12
S28 3	235745	mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 17:15

S28 4	840	S281 and S283	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 17:15
S28 5	238265	mosfet or (metal adj oxide adj semiconductor adj (fet or field)) or pmos or cmos or nmos or misfet or complement\$6 near (mosfet misfet metal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 17:15
S28 6	847	S281 and S285	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 17:15
S28 7	407	S281 and S285 and S282	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 17:31
S28 8	104	S287 and (@ad < "20021030")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 17:31
S28 9	1965	S280 and S285 and S282	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 17:26
S29 0	4063	S280 with channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 17:26
S29 1	526	S290 and S285 and S282	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 17:26
S29 2	146	S291 and (@ad < "20021030")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 17:29
S29 3	33381	silicon near2 germanium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 17:29

S29 4	542	"si.sub.x ge.sub.1-x"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 17:29
S29 5	413	"si.sub.xge.sub.1-x"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 17:29
S29 6	76	"si.sub.x ge.sub.y"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 17:29
S29 7	74	"si.sub.y ge.sub.1-y" "si.sub.yge.sub. 1-y"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 17:29
S29 8	1105	"si.sub.1-x ge.sub.x" "si.sub.1-xge. sub.x"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 17:29
S29 9	206	"si.sub.1-y ge.sub.y" "si.sub.1-yge. sub.y"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 17:29
S30 0	34048	S294 or S295 or S296 or S297 or S298 or S299 or S293	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 17:29
S30 1	3354534	si silicon germanium sige gesi sic carbon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 17:29
S30 2	3754922	si silicon germanium sige gesi sic carbon iv	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 17:30
S30 3	3754421	si silicon germanium sige gesi sic carbon iv!	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 17:30

S30 4	7953	S280 near4 S303	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 17:30
S30 5	1054	S304 and S285 and S282	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 18:14
S30 6	380	S305 and (@ad < "20021030")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 18:14
S30 7	268	S304 same S282 and S285	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/15 14:24
S30 8	91	S307 and (@ad < "20021030")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 18:15

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L9	169	amberwave.as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/15 14:51
L10	139	1 and 9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/15 14:52
L11	0	1 and 9 and 2 with screen\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/15 14:52